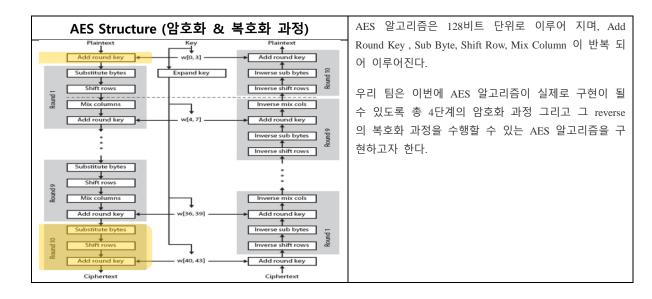
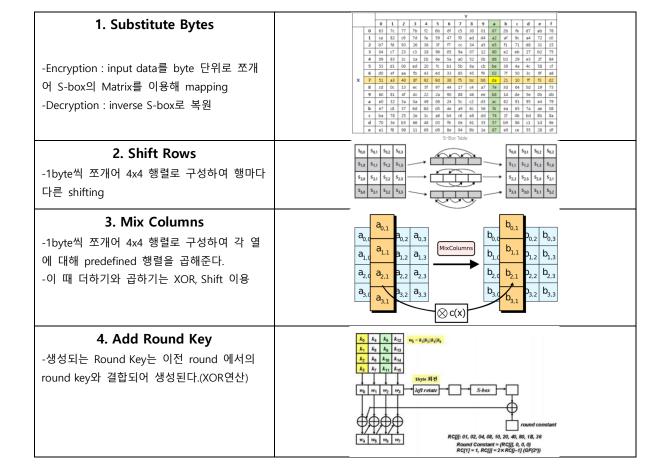
VLSI System Design (prof. Jinsang Kim) Term Project Final Report (18a)

Subject: Advanced Encryption Standard(AES) Algorithm

RTL Simulation Result





Hierarchy structure of Verilog Code.

AES_ERC_PAD.v								
AES_ERC.v (TOP CELL)								
Subkeys.v			AES_pipe.v					
Columns.v				AES_col.v				
Xor_tree.v	Prod_gen.v		Shift_rows.v	al ·	Columns.v			
	Multiply_by_2_pow_n.v					Prod_gen.v		
	Multiply_by_2.v	Switch_gates.v		Sbox_mi.v	Xor_tree.v	Multiply_by_2_pow_n.v		
						Multiply_by_2.v Switch_gates.v		

Verilog Code List

AES_ERC_PADS.v : Top cell 에 붙는 PAD 를 연결하기 위한 cell.

AES_ERC.v : TOP cell

(out,out_valid,out_ready,in,in_valid,in_ready,dec,clk,rst,size)

Subkey.v : 암호화와 복호화를 위한 Subkey를 load. 입력된 data의 Mix column 작업 또

한 수행한다.

AES_pipe.v : 1번의 round 를 수행하는 cell.

Shift_row.v : 입력된 data 를 1byte 단위로 쪼개어 행 별로 1번씩 shift 시켜줌.

AES col.v : 각각의 column 에 대해 sbox 에 매핑하여 변환하고, Mix column 작업 수행

Sbox_mi.v : S-box 의 look up table 이 있으며, 1개 column 에 대해 매핑 및 변환 작업

수행.

Columns.v : Mix column 작업 수행.

Xor_tree.v : 입력된 1byte씩의 4개 data 에 대해 XOR 연산을 수행하여 1개의 1byte 출력

data 생성하는 cell.

Prod_gen.v : Columns.v cell 과 해당 작업을 수행하기 위한 하위 cell 간의 연결 cell. (key,

data) 및 다음 작업을 위한 새로운 round key 생성.

Multiply_by_2_pow_n.v : 입력된 1byte의 data를 총 8배 곱셈 연산하는 cell.

Multiply_by_2.v : 입력된 1byte의 data를 2배 시켜줌.

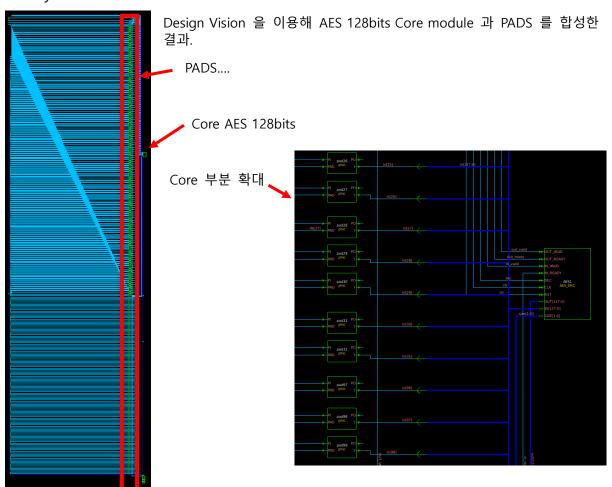
Switch_gates.v : 입력된 data 를 inverter를 통과시켜 data를 flip 시킴.

I/O description.

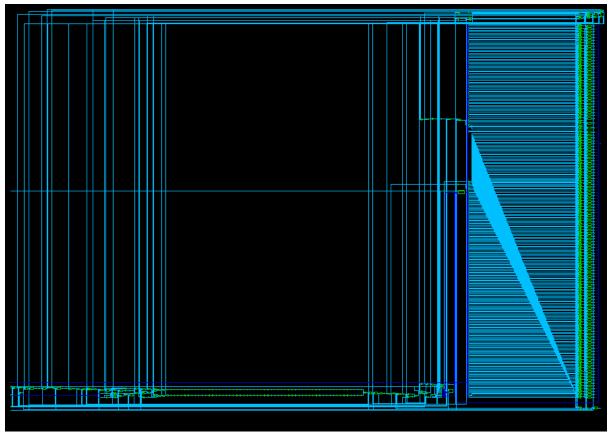
[out, out_valid, out_ready, in, in_valid ,in_ready ,dec, clk, rst, size]

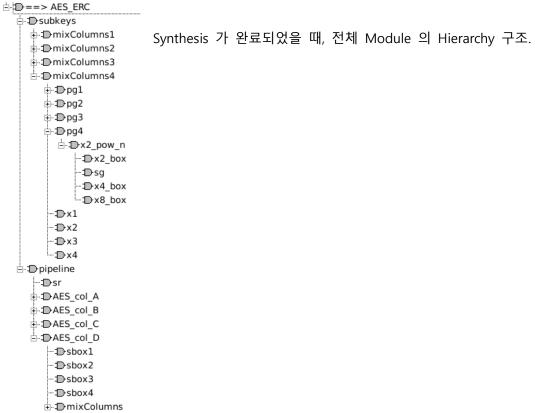
Pin	Direction	Description		
In[0:127]	INPUT	Data Input		
Dec	INPUT	Decryption (복호화) flag (encryption : 0, decryption : 1)		
Size[0:1]	INPUT	Key length flag (128bits : 0, 192bits : 1, 256bits: 2, don't use : 3)		
Out[0:127]	OUTPUT	Data Output		
In_valid	INPUT	Data Input is valid		
In_ready	INPUT	Input is ready for Data (when it falling 1 -> 0. Last input is input data.)		
Out_valid	OUTPUT	Data Output is valid		
Out_ready	OUTPUT	Output is ready for Data		
Clk	INPUT	Clock		
Rst	INPUT	Reset		

RTL Synthesis Result



Core Module (AES_ERC) 내부 Schematic



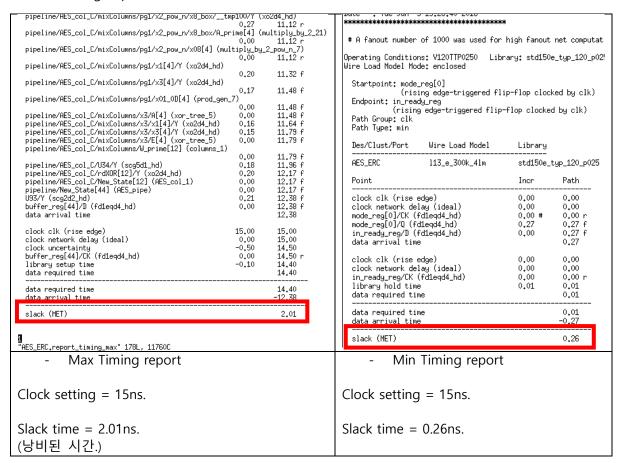


Synthesis Report

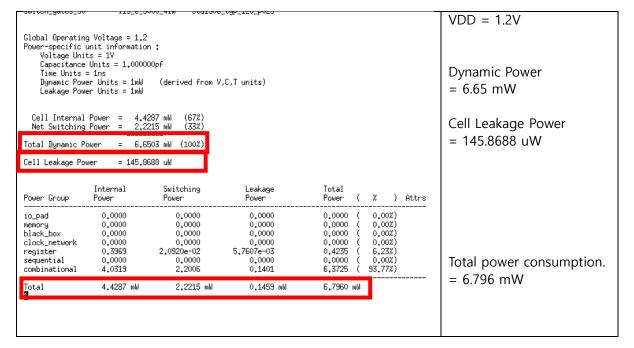
- Area Report

Report : area Design : NAND Version: F-2011.09-SP5-3 Date : Tue Jun 5 14:49:57 2018 ************************************	사용된 Gate 수를 Estimate 하기 위해서 간단한 AND gate를 synthesis 하여 단일 cell 이차지하는 Area를 확인함.		
Library(s) Used: std150e_typ_120_p025 (File: /Tools/Library/	→ 3.68872um ²		
Number of ports: 3 Number of nets: 3 Number of cells: 1 Number of combinational cells: 1 Number of sequential cells: 0 Number of macros: 0 Number of buf/inv: 0 Number of references: 1			
Combinational area: 3.666670 Buf/Inv area: 0.000000 Noncombinational area: 0.000000 Net Interconnect area: 0.022050			
Total area: 3,088720			
Report : area Design : AES_ERC Version: F-2011.09-SP5-3 Date : Tue Jun 5 14:13:18 2018 ***********************************	Total Area: 202,334 um ² The Number of Gate = $\frac{202334.689538}{2.68872}$		
Library(s) Used:	=54,852.27 3.68872		
std150e_typ_120_p025 (File: /Tools/Library/samsung013/ser Number of ports: 265 Number of nets: 881 Number of cells: 488 Number of combinational cells: 348 Number of sequential cells: 138 Number of macros: 0 Number of buf/inv: 151 Number of references: 33	약 54,850 개의 Gate 사용됨.		
Combinational area: 178816.807381 Buf/Inv area: 25684.674480 Noncombinational area: 22575.658727 Net Interconnect area: 942.222430			
Total area: 202334,689538			

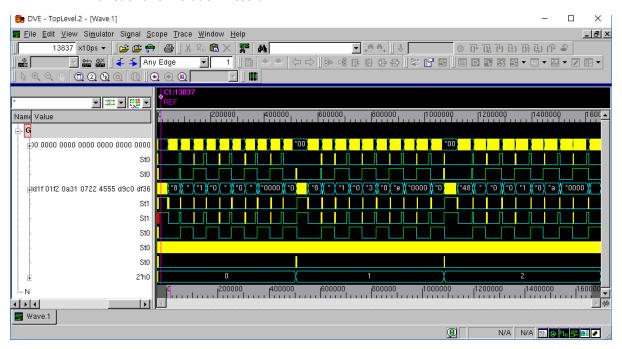
Timing Report



- Power Report

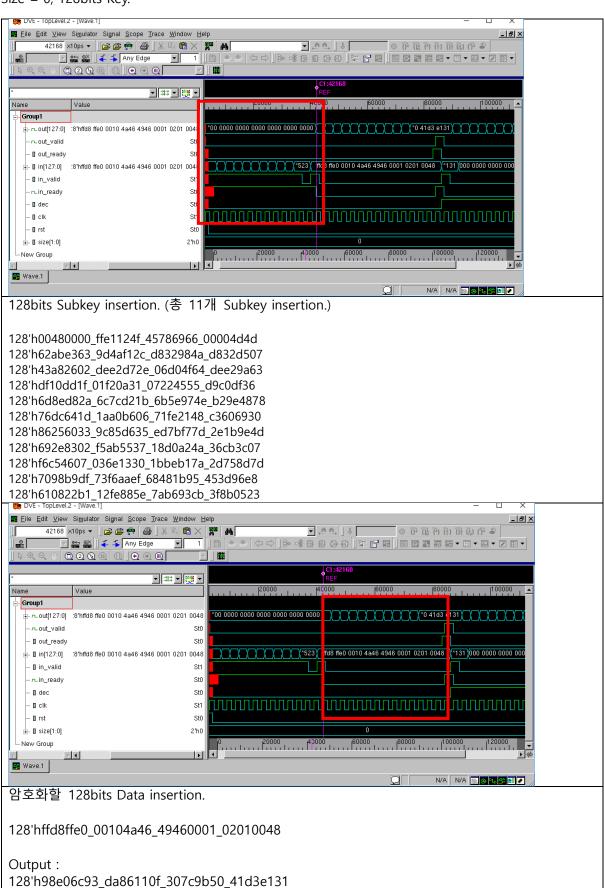


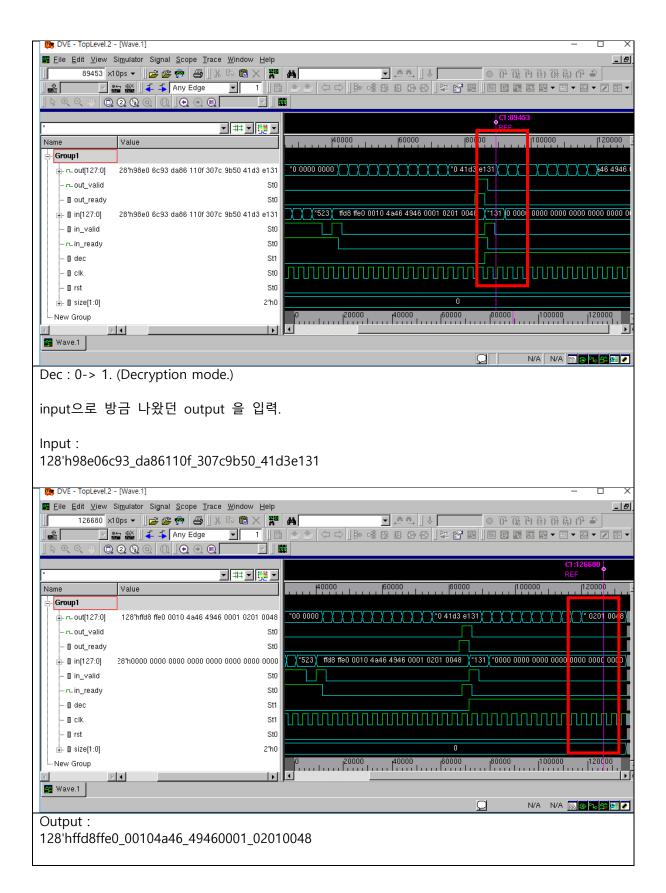
- DVE Functional Simulation Result



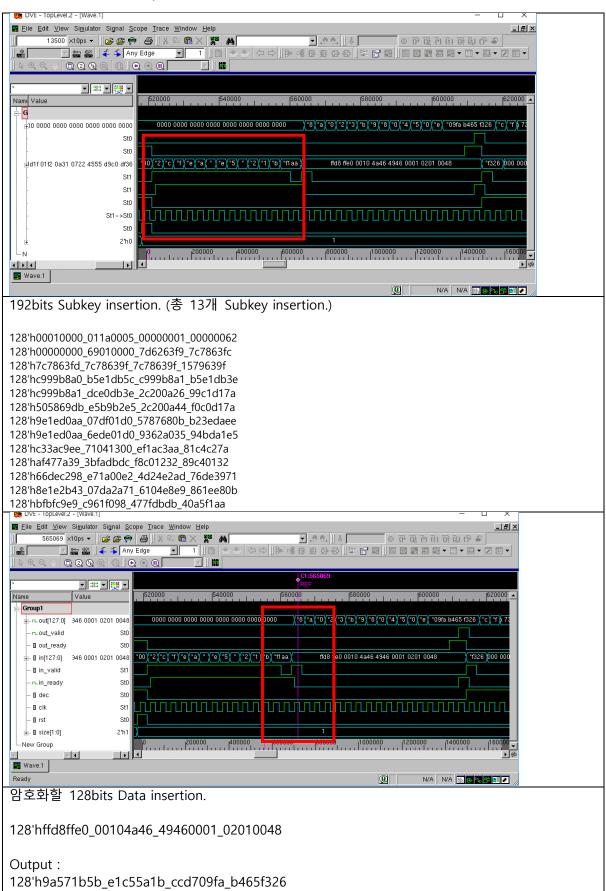
Testbench를 이용하여, 각각의 경우에 대해 (Size = 0, 1, 2), functional simulation 진행.

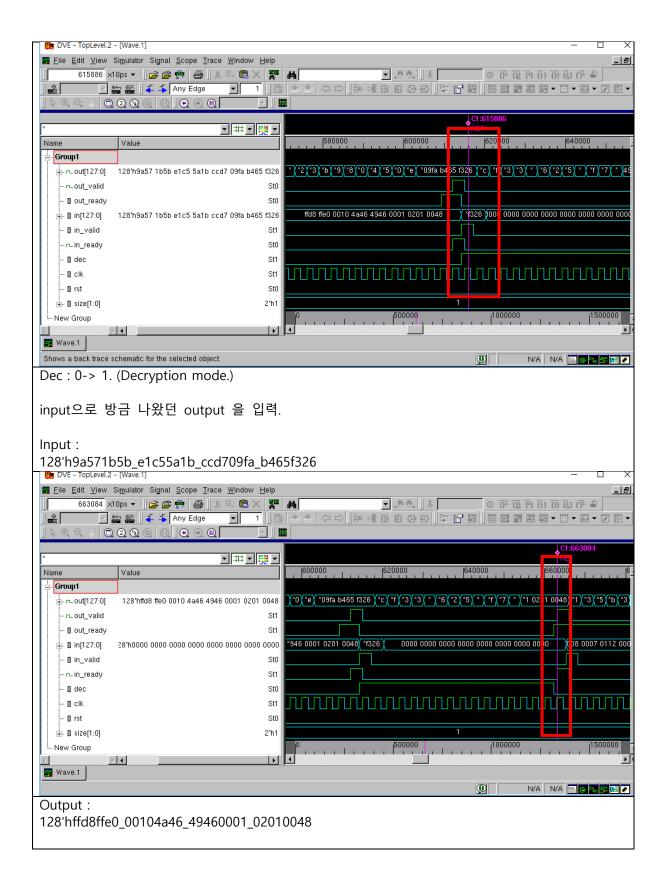
Size = 0, 128bits Key.



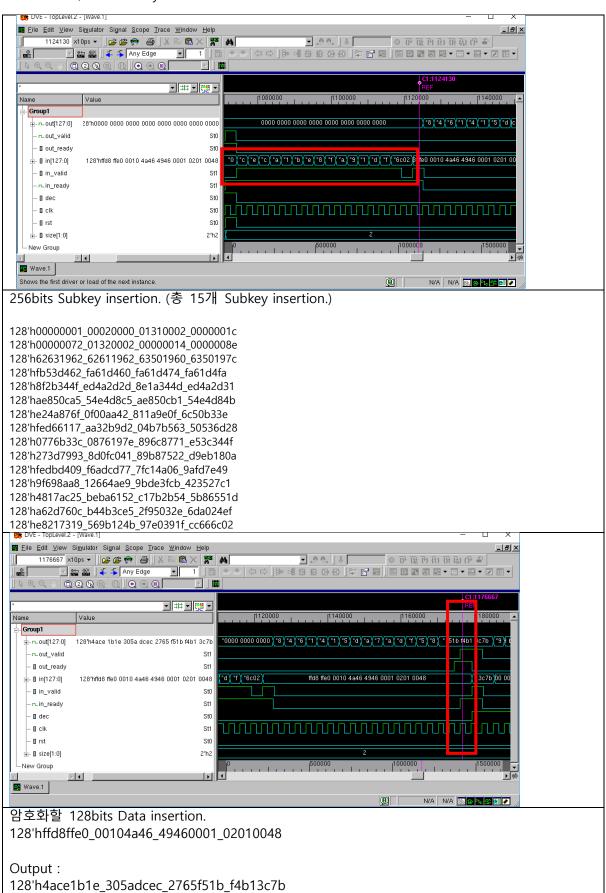


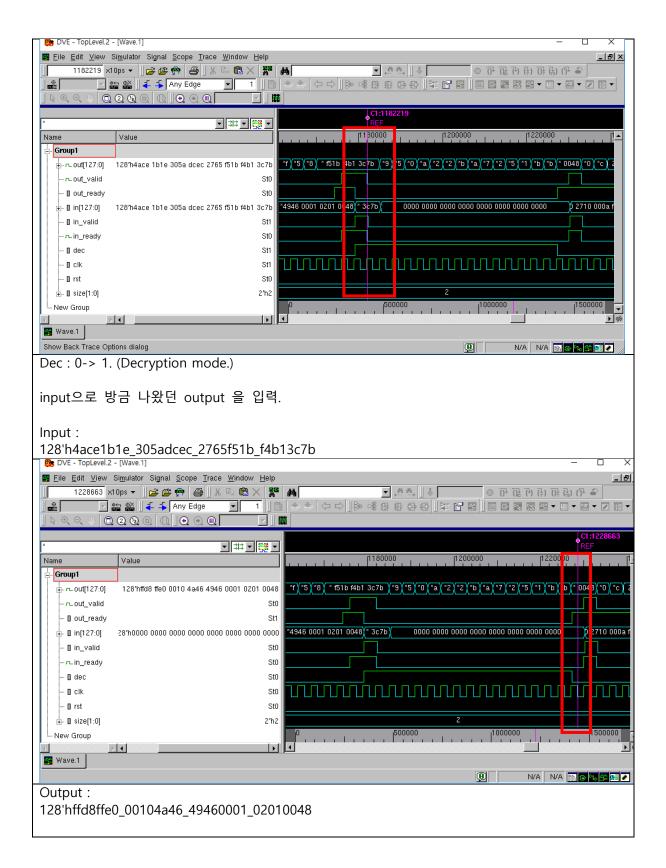
Size = 1, 192 bits key.





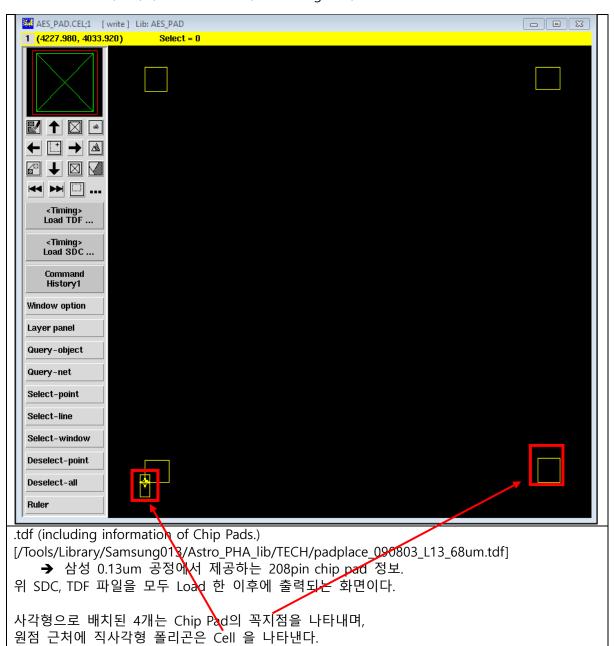
Size = 2, 256 bits key.

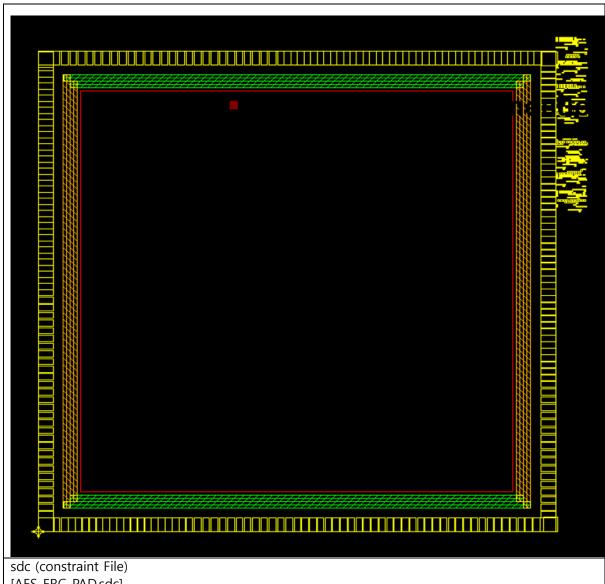




Astro(Place & Route)

ASTRO Tool 을 이용하여 cell을 Place 하고 Routing 한다.





[AES_ERC_PAD.sdc]

→ RTL Synthesis 이후에 함께 출력되는 파일.

SDC 파일을 통해 생성된 Cell을 chip Area에 흩뿌린다.

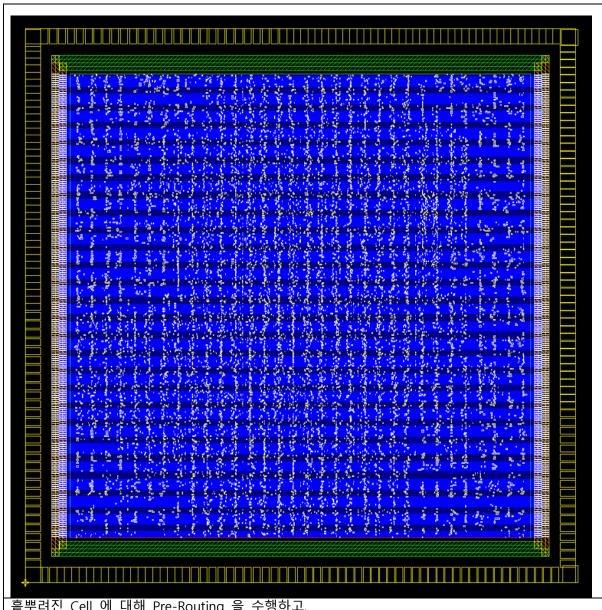
Floor Planner 를 통해 Chip Space 생성.

총 208 pin 의 PADS 가 chip 가장 자리에 잡았으며,

흩뿌려진 전체 Cell의 크기는 Chip 내부에 붉은색 사각형으로 나타난다.

위와 같이 붉은색 사각형이 Chip 내부 영역에 형성되어 있다.

이후 GND, VDD 를 위한 Power Ring을 형성한다.



흩뿌려진 Cell 에 대해 Pre-Routing 을 수행하고, Standard Cell 을 mapping 함.

